

October 2007 STEALTHTM II Rectifier

FFP15S60S

Features

- High Speed Switching, t_{rr} < 35ns @ I_F = 15A
- · High Reverse Voltage and High Reliability
- · RoHS compliant

Applications

- · General Purpose
- Switching Mode Power Supply
- Boost Diode in continuous mode power factor corrections
- · Power switching circuits



15A, 600V STEALTH™ II Rectifier

The FFP15S60S is STEALTH TM II rectifier with soft recovery characteristics. It is silicon nitride passivated ion-implanted epitaxial planar construction.

This device is intended for use as freewheeling of boost diode in switching power supplies and other power switching applications. Their low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits reducing power loss in the switching transistors.



Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{RRM}	Peak Repetitive Reverse Voltage	600	V
V_{RWM}	Working Peak Reverse Voltage	600	V
V _R	DC Blocking Voltage	600	V
I _{F(AV)}	Average Rectified Forward Current @ T _C = 123°C	15	Α
I _{FSM}	Non-repetitive Peak Surge Current 60Hz Single Half-Sine Wave	150	А
T _J , T _{STG}	Operating and Storage Temperature Range	-65 to +150	°C

Thermal Characteristics

Symbol	Parameter	Ratings	Units
R_{\thetaJC}	Maximum Thermal Resistance, Junction to Case	1.3	°C/W

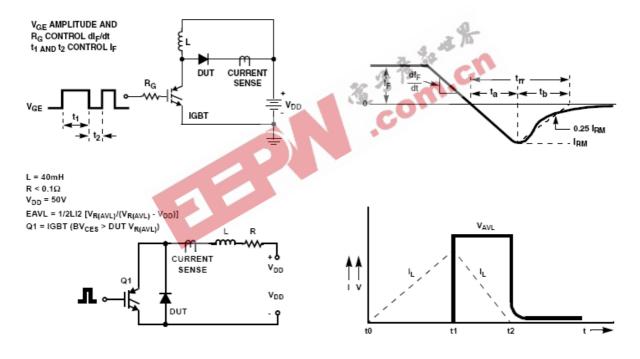
Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
F15S60S	FFP15S60STU	TO-220-2L	-	-	50

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter		Min.	Тур.	Max.	Units
V _{FM} 1	I _F = 15A I _F = 15A	$T_{\rm C} = 25^{\rm o}{\rm C}$ $T_{\rm C} = 125^{\rm o}{\rm C}$		2.1 1.6	2.6	V
I _{RM} 1	V _R = 600V V _R = 600V	$T_{C} = 25^{\circ}C$ $T_{C} = 125^{\circ}C$			100 500	μА
t _{rr}	$I_F = 1A$, di/dt = 100A/ μ s, $V_R = 30V$	$T_{\rm C} = 25^{\rm o}{\rm C}$	-	21	30	ns
t _{rr} I _{rr} S factor Q _{rr}	$I_F = 15A$, di/dt = 200A/ μ s, $V_R = 390V$	T _C = 25°C	- - -	23 2.5 0.7 29	35 - - -	ns A nC
t _{rr} I _{rr} S factor Q _{rr}	$I_F = 15A$, di/dt = 200A/ μ s, $V_R = 390V$	T _C = 125°C	- - -	55 4.3 1.1 118	- - -	ns A nC
W _{AVL}	Avalanche Energy (L = 40mH)		20	-	-	mJ

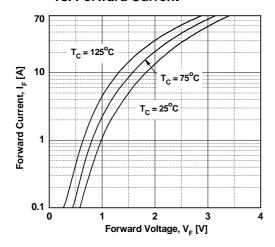
Test Circuit and Waveforms



Notes: 1: Pulse: Test Pulse width = 300μ s, Duty Cycle = 2%

Typical Performance Characteristics

Figure 1. Typical Forward Voltage Drop vs. Forward Current



vs. Reverse Voltage 100

Figure 2. Typical Reverse Current

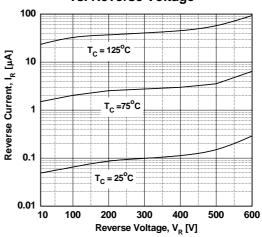


Figure 3. Typical Junction Capacitance

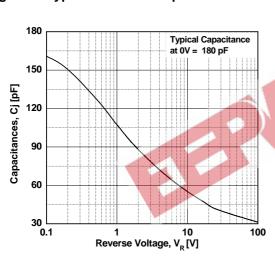


Figure 4. Typical Reverse Recovery Time vs. di/dt

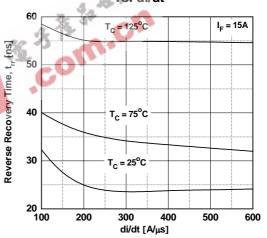


Figure 5. Typical Reverse Recovery Current vs. di/dt

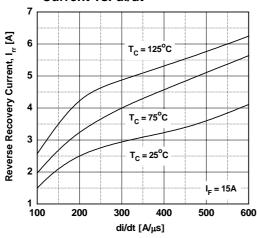
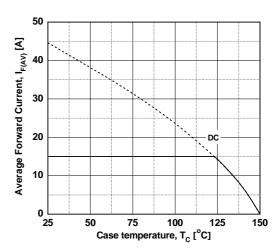
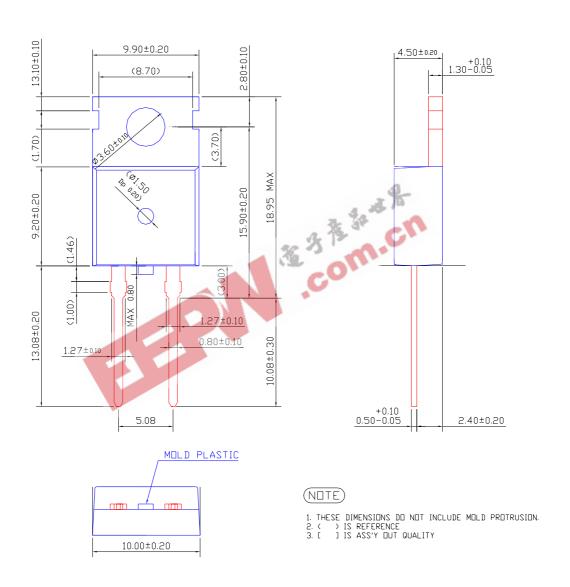


Figure 6. Forward Current Derating Curve



Mechanical Dimensions

TO-220-2L





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